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Applicant: Lee et al.
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 Title: TREATMENT FOR CORROSION IN
 SUBSTRATE PROCESSING

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INFORMATION DISCLOSURE STATEMENT

US PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number	Publication Date	Name of Patentee or Applicant	Reference to Related Case
du	1	3,398,033	08/1968	Haga et al.	
	2	4,595,453	06/1986	Yarmazaki et al.	
	3	4,351,894	09/1982	Yonezawa et al.	
	4	4,865,685	09/1989	Palmour et al.	
	5	4,981,551	01/1991	Palmour et al.	
	6	6,090,304	07/2000	Zhu et al.	
	7	6,261,892	07/2001	Swanson	
	8	6,528,426	03/2003	Olsen et al.	
	9	5,981,551	11/1999	Luengo et al.	
	10	6,743,725	06/2004	Hu et al.	
	11	6,617,244	09/2003	Nishizawa	
	12	5,756,400	05/1998	Ye et al.	
	13	5,626,775	05/1997	Roberts et al.	
	14	6,040,248	2000-03-21	Chen et al.	
	15	6,399,424	2002-06-04	Matsuura et al.	
	16	4,735,920	1988-04-05	Stephanie et al.	
	17	5,254,215	1993-10-19	Terakado et al.	
	18	5,356,478	1994-10-18	Chen et al.	
	19	5,647,953	1997-07-15	Williams et al.	
	20	5,681,424	1997-10-28	Saito et al.	
	21	5,756,400	1998-05-26	Ye et al.	
	22	5,770,523	1998-06-23	Hung et al.	
	23	5,817,578	1998-10-06	Ogawa	
	24	5,820,723	1998-10-13	Benjamin et al.	
	25	5,928,967	1999-07-27	Radens et al.	
	26	6,074,514	2000-06-13	Bjorkman et al.	
	27	6,136,211	2000-10-24	Qian et al.	
	28	6,153,935	2000-11-28	Edelstein et al.	
	29	6,284,657	2001-09-04	Chooi et al.	
	30	6,211,032	2001-04-03	Redford et al.	
	31	6,103,590	2000-08-15	Swanson et al.	
	32	6,387,819	2002-05-14	Yu	
	33	6,284,149	2001-09-04	Li et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number	Publication Date	Name of Patentee or Applicant	Pages, Columns, Lines, Where Relevant Information Appears	T
dl	34	EP 0926715A2	1999-06-30	Europe		
	35	DE 4310345A1	1994-10-06	Germany		
	36	EP 0600664A2	1994-06-08	Europe		
	37	WO 9952135A	1999-10-14	WIPO		
	38	JP 2001102447A	2001-04-13	Japan		
	39	JP 63-152125	1998-06-24	Japan		

OTHER DOCUMENTS

Examiner Initials	Cite No.	Description	T
dl	40	Lo, T.C. et al., "Reactive ion etching of a-SiC:H films using CCl ₄ and O ₂ gas mixture", Journal of Vacuum Science and Technology: Part A, American Institute of Physics., New York, US, Vol. 11, No. 2, march 1, 1993.	
	41	PCT International Search Report, PCT/US02/21863 dated January 29, 2003	
	42	Moalem et al., "Low-temperature vapor-phase etching of silicon carbide by dioxygen difluoride", Applied Phys. Lett., 1995, pp. 3480-3482, Vol. 66(25), American Institute of Physics, New York, USA	
	43	US Application No.: 10/430,013; Filing Date: May 6, 2003; Inventors: Si Yi Li	
	44	US Application No.: 10/623,018; Filing Date: July 17, 2003; Inventors: Kang	
dl	45	US Application No.: 10/623,017; Filing Date: July 17, 2003; Inventors: Lee et al.	

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